



**Product Description**

The SGA5286Z is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring one-micron emitters provides high  $F_T$  and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.

**Features**

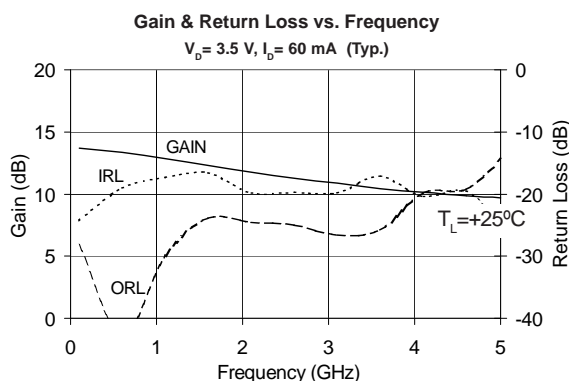
- High Gain: 12.0dB at 1950MHz
- Cascadable 50 $\Omega$
- Operates from Single Supply
- Low Thermal Resistance Package

**Applications**

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

**Optimum Technology Matching® Applied**

- GaAs HBT
- GaAs MESFET
- InGaP HBT
- SiGe BiCMOS
- Si BiCMOS
- SiGe HBT
- GaAs pHEMT
- Si CMOS
- Si BJT
- GaN HEMT
- RF MEMS



Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Small Signal Gain	12.2	13.5	14.9	dB	850MHz
		12.0		dB	1950MHz
		11.5		dB	2400MHz
Output Power at 1dB Compression		17.0		dBm	850MHz
		14.0		dBm	1950MHz
Output Third Intercept Point		31.0		dBm	850MHz
		27.2		dBm	1950MHz
Bandwidth Determined by Return Loss		5000		MHz	>10dB
Input Return Loss		19.5		dB	1950MHz
Output Return Loss		24.4		dB	1950MHz
Noise Figure		4.9		dB	1950MHz
Device Operating Voltage	3.1	3.5	3.9	V	
Device Operating Current	54	60	66	mA	
Thermal Resistance (Junction - Lead)		97		$^{\circ}\text{C}/\text{W}$	

Test Conditions:  $V_S=8\text{V}$ ,  $I_D=60\text{mA}$  Typ.,  $OIP_3$  Tone Spacing = 1MHz,  $P_{OUT}$  per tone = -5dBm,  $R_{BIAS}=75\Omega$ ,  $T_L=25^{\circ}\text{C}$ ,  $Z_S=Z_L=50\Omega$

## Absolute Maximum Ratings

Parameter	Rating	Unit
Max Device Current ( $I_D$ )	120	mA
Max Device Voltage ( $V_D$ )	5	V
Max RF Input Power	+16	dBm
Max Junction Temp ( $T_J$ )	+150	°C
Operating Temp Range ( $T_L$ )	-40 to +85	°C
Max Storage Temp	+150	°C



**Caution!** ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

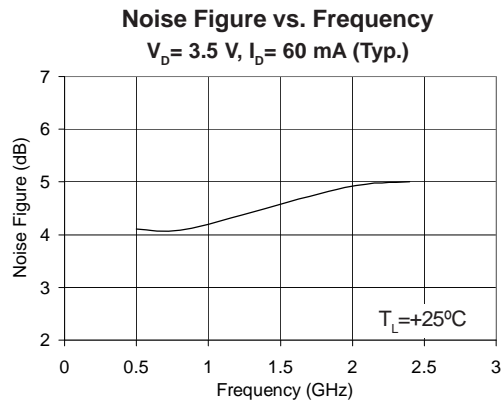
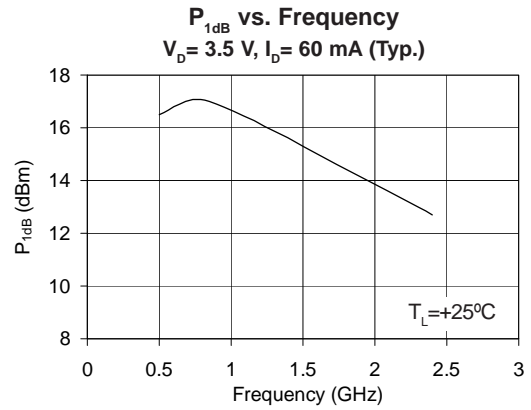
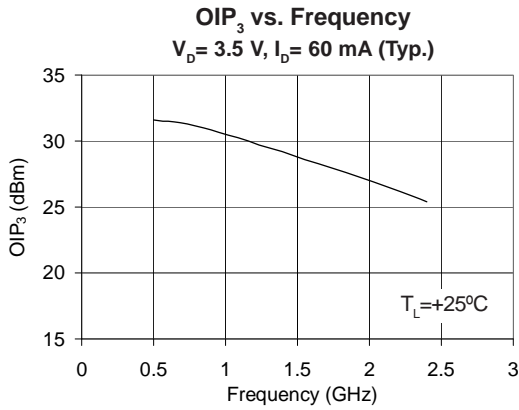
Bias Conditions should also satisfy the following expression:

$$I_D V_D < (T_J - T_L) / R_{TH, J-I}$$

## Typical Performance at Key Operating Frequencies

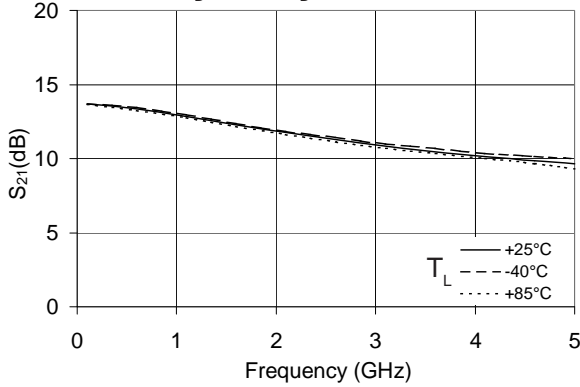
Parameter	Unit	100 MHz	500 MHz	850 MHz	1950 MHz	2400 MHz	3500 MHz
Small Signal Gain	dB	13.7	13.6	13.5	12.0	11.5	10.5
Output Third Order Intercept Point	dBm		31.6	31.0	27.2	25.4	
Output Power at 1dB Compression	dBm		16.5	17.0	14.0	12.7	
Input Return Loss	dB	24.2	20.4	17.1	19.5	19.4	16.7
Output Return Loss	dB	28.2	34.5	35.3	24.4	23.8	26.2
Reverse Isolation	dB	17.7	18.0	18.4	19.2	19.5	19.5
Noise Figure	dB		4.1	4.1	4.9	5.0	

Test Conditions:  $V_S = 8V$ ,  $I_D = 60mA$  Typ., OIP<sub>3</sub> Tone Spacing = 1MHz, P<sub>OUT</sub> per tone = -5dBm, R<sub>BIAS</sub> = 75Ω, T<sub>L</sub> = 25°C, Z<sub>S</sub> = Z<sub>L</sub> = 50Ω



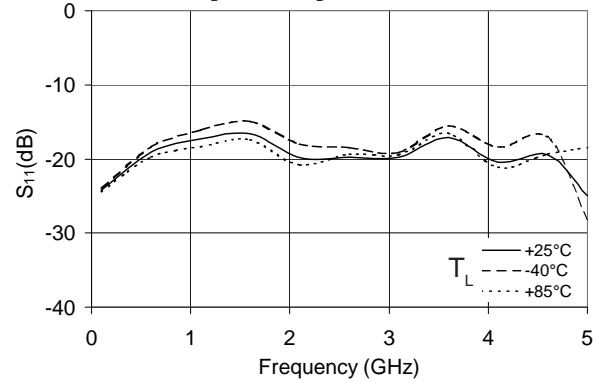
**$|S_{21}|$  vs. Frequency**

$V_D = 3.5$  V,  $I_D = 60$  mA (Typ.)



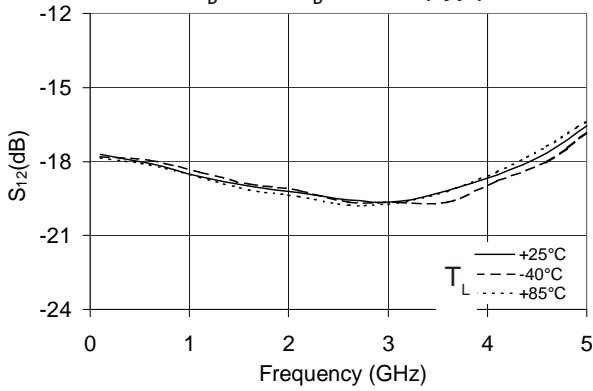
**$|S_{11}|$  vs. Frequency**

$V_D = 3.5$  V,  $I_D = 60$  mA (Typ.)



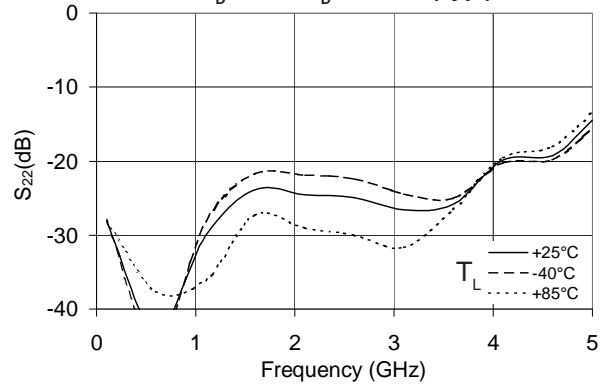
**$|S_{12}|$  vs. Frequency**

$V_D = 3.5$  V,  $I_D = 60$  mA (Typ.)



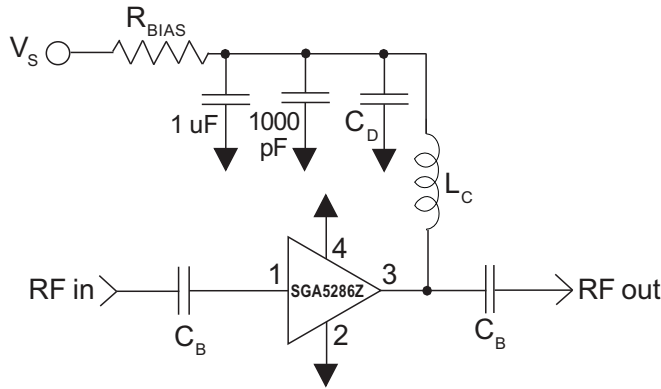
**$|S_{22}|$  vs. Frequency**

$V_D = 3.5$  V,  $I_D = 60$  mA (Typ.)



Pin	Function	Description
1	RF IN	RF input pin. This pin requires the use of an external DC-blocking capacitor chosen for the frequency of operation.
2, 4	GND	Connection to ground. For optimum RF performance, use via holes as close to ground leads as possible to reduce lead inductance.
3	RF OUT/BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC-blocking capacitor is necessary for proper operation.

**Application Schematic**

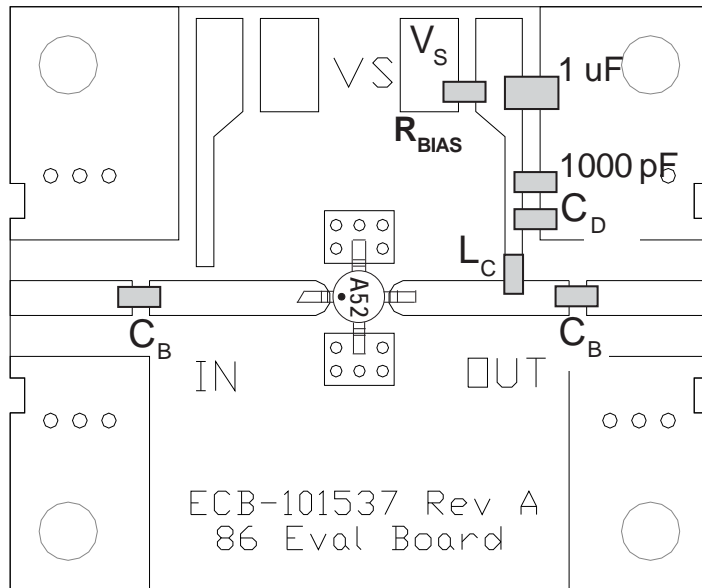


Reference Designator	Frequency (Mhz)				
	500	850	1950	2400	3500
C <sub>B</sub>	220 pF	100 pF	68 pF	56 pF	39 pF
C <sub>D</sub>	100 pF	68 pF	22 pF	22 pF	15 pF
L <sub>C</sub>	68 nH	33 nH	22 nH	18 nH	15 nH

Recommended Bias Resistor Values for I <sub>D</sub> =60mA				
$R_{BIAS} = (V_S - V_D) / I_D$				
Supply Voltage(V <sub>S</sub> )	6 V	8 V	10 V	12 V
R <sub>BIAS</sub>	43 Ω	75 Ω	110 Ω	150 Ω

Note: R<sub>BIAS</sub> provides DC bias stability over temperature.

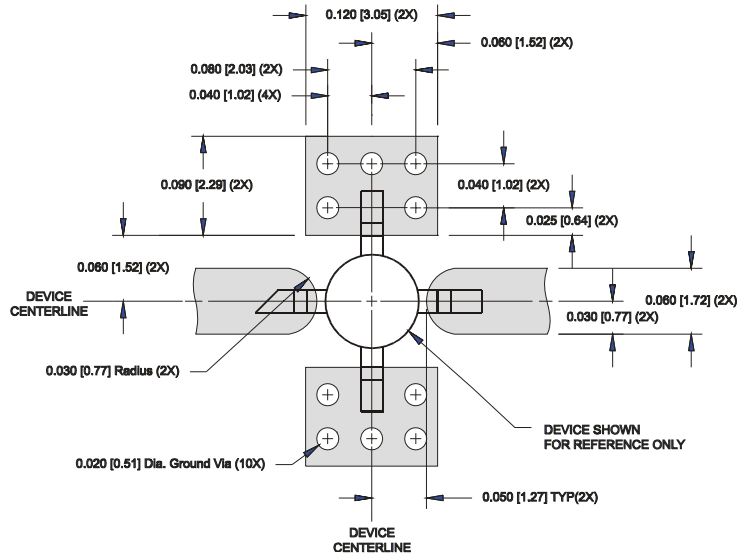
**Evaluation Board Layout**



**Mounting Instructions**

1. Use a large ground pad area under device pins 2 and 4 with many plated through-holes as shown.
2. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

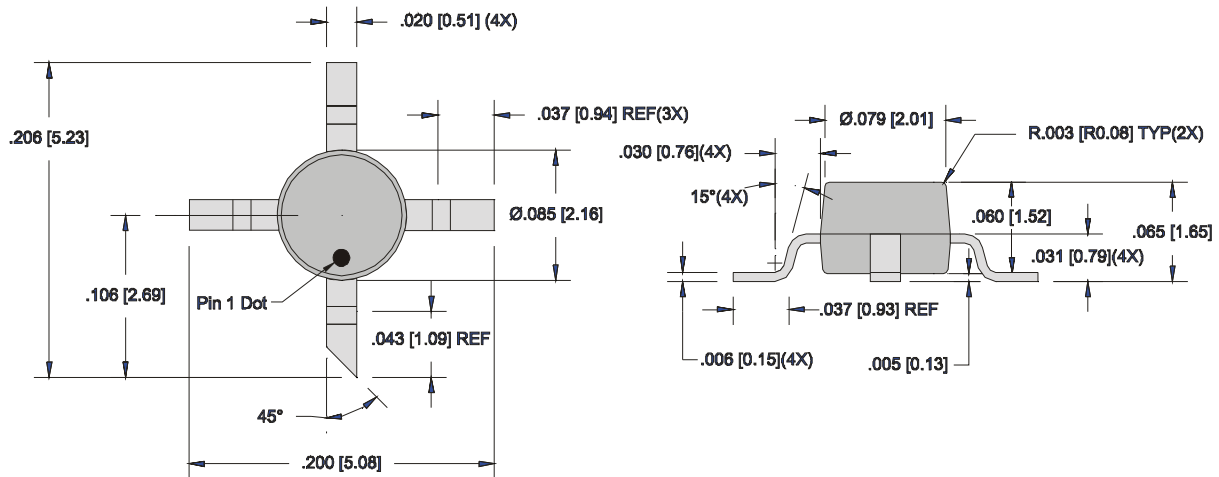
## Suggested Pad Layout



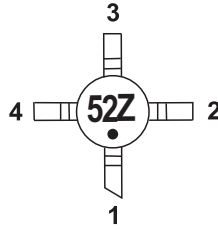
## Package Drawing

Dimensions in inches (millimeters)

Refer to drawing posted at [www.rfmd.com](http://www.rfmd.com) for tolerances.



**Part Identification**



**Ordering Information**

Ordering Code	Description
SGA5286Z	13" Reel with 3000 pieces
SGA5286ZSQ	Sample bag with 25 pieces
SGA5286ZSR	7" Reel with 100 pieces
SGA5286ZPCK1	850MHz, 8V Operation PCBA with 5-piece sample bag